

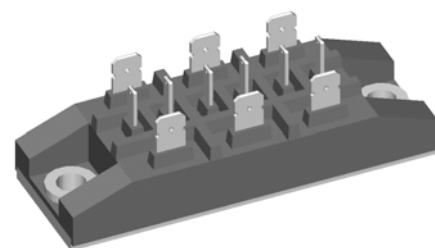
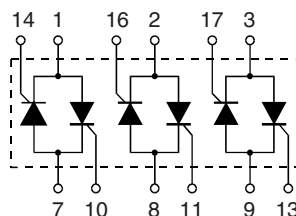
Three Phase AC Controller Modules

$$I_{RMS} = 3 \times 60 \text{ A}$$

$$V_{RRM} = 1200-1600 \text{ V}$$

Preliminary data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
1200	1200	VWO 60-12io7
1400	1400	VWO 60-14io7
1600	1600	VWO 60-16io7



Symbol	Conditions	Maximum Ratings	
I_{RMS}	$T_K = 85^\circ\text{C}$, 50 - 400 Hz (per phase)	60	A
I_{TRMS}	$T_{VJ} = T_{VJM}$	43	A
I_{TAVM}	$T_K = 85^\circ\text{C}$; (180° sine)	27	A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine	550 A
		t = 8.3 ms (60 Hz), sine	600 A
	$T_{VJ} = T_{VJM}$	t = 10 ms (50 Hz), sine	500 A
	$V_R = 0$	t = 8.3 ms (60 Hz), sine	550 A
I^2t	$T_{VJ} = 45^\circ\text{C}$	t = 10 ms (50 Hz), sine	1520 A ² s
	$V_R = 0$	t = 8.3 ms (60 Hz), sine	1520 A ² s
	$T_{VJ} = T_{VJM}$	t = 10 ms (50 Hz), sine	1250 A ² s
	$V_R = 0$	t = 8.3 ms (60 Hz), sine	1250 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 50 Hz, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.45 \text{ A}$ $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	repetitive, $I_T = 25 \text{ A}$	150 A/ μs
		non repetitive, $I_T = I_{TAVM}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	1000 V/ μs
P_{GM}	$T_{VJ} = T_{VJM}$	$t_p = 30 \mu\text{s}$	10 W
	$I_T = I_{TAVM}$	$t_p = 300 \mu\text{s}$	5 W
P_{GAVM}			0.5 W
V_{RGM}			10 V
T_{VJ}		-40...+125	°C
T_{VJM}		125	°C
T_{stg}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS	t = 1 min	2500 V~
	$I_{ISOL} \leq 1 \text{ mA}$	t = 1 s	3000 V~
M_d	Mounting torque (M5) (10-32 UNF)	5 ± 15 %	Nm
		44 ± 15 %	lb.in.
Weight	typ.	110	g

Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- Package with metal base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- UL applied
- 1/4" fast-on power terminals

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- Solid state switches
- Light and temperature control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Light weight and compact

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.

Symbol	Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	$\leq$	5	mA
V_T	$I_T = 45 \text{ A}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.45	V
V_{T0}	For power-loss calculations only		0.85	V
r_T			11	mΩ
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.5	V
	$T_{VJ} = -40^\circ\text{C}$	$\leq$	1.6	V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	$\leq$	100	mA
	$T_{VJ} = -40^\circ\text{C}$	$\leq$	200	mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	$\leq$	0.2	V
I_{GD}		$\leq$	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$\leq$	450	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	$\leq$	200	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$\leq$	2	μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}; t_p = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	150	μs
R_{thJC}	per thyristor; sine 180°el		0.9	K/W
	per module		0.15	K/W
R_{thJK}	per thyristor; sine 180°el		1.1	K/W
	per module		0.183	K/W
d_s	Creeping distance on surface		16.1	mm
d_A	Creepage distance in air		6.0	mm
a	Max. allowable acceleration		50	m/s ²

Dimensions in mm (1 mm = 0.0394")

